Andrew G Norman

List of Publications by Year
in descending order

189 papers	6,092 citations	94433 37 h-index	82547 72 g-index
191 all docs	191 docs citations	191 times ranked	6576 citing authors

#	Article	IF	Citations
1	Multiscale Characterization of Photovoltaic Modulesâ€”Case Studies of Contact and Interconnect Degradation. IEEE Journal of Photovoltaics, 2022, 12, 62-72.	2.5	10
2	High Mobility Cd₃As₂(112) on GaAs(001) Substrates Grown via Molecular Beam Epitaxy. ACS Applied Electronic Materials, 2022, 4, 729-734.	4.3	4
3	Epitaxial Dirac Semimetal Vertical Heterostructures for Advanced Device Architectures. Advanced Functional Materials, 2022, 32, .	14.9	11
4	Evolution of solid electrolyte interphase and active material in the silicon wafer model system. Journal of Power Sources, 2021, 482, 228946.	7.8	19
5	Application of templated vapor-liquid-solid growth to heteroepitaxy of InP on Si. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2021, 39, 013404.	2.1	4
6	Tandem Heterogeneous Catalysis for Polyethylene Depolymerization via an Olefin-Intermediate Process. ACS Sustainable Chemistry and Engineering, 2021, 9, 623-628.	6.7	85
7	Insights into the Dynamic Interfacial and Bulk Composition of Copper-Modified, Hydrogen-Alloyed, Palladium Nanocubes under Electrocatalytic Conditions. Journal of Physical Chemistry C, 2021, 125, 15487-15495.	3.1	1
8	Performance and reliability of Î²-Ga2O3 Schottky barrier diodes at high temperature. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2021, 39, .	2.1	19
9	Surface conversion of single-crystal Bi2Se3 to Î²-In2Se3. Journal of Crystal Growth, 2021, 573, 126306.	1.5	0
10	Mg _x Zn_{1âˆ’x}O contact to CuGa₃Se₅ absorber for photovoltaic and photoelectrochemical devices. JPhys Energy, 2021, 3, 024001.	5.3	10
11	Accelerating Hydrogen Absorption and Desorption Rates in Palladium Nanocubes with an Ultrathin Surface Modification. Nano Letters, 2021, 21, 9131-9137.	9.1	15
12	Growth of GaAs on single-crystal layered-2D Bi2Se3. Journal of Crystal Growth, 2020, 534, 125457.	1.5	2
13	Optical and Structural Properties of High-Efficiency Epitaxial Cu(In,Ga)Se₂ Grown on GaAs. ACS Applied Materials & Interfaces, 2020, 12, 3150-3160.	8.0	11
14	Improving Interface Stability of Si Anodes by Mg Coating in Li-Ion Batteries. ACS Applied Energy Materials, 2020, 3, 11534-11539.	5.1	10
15	Microscopic Observation of Solid Electrolyte Interphase Bilayer Inversion on Silicon Oxide. ACS Energy Letters, 2020, 5, 3657-3662.	17.4	26
16	High-Temperature Nucleation of GaP on V-Grooved Si. Crystal Growth and Design, 2020, 20, 6745-6751.	3.0	10
17	Sputtered p-Type Cu_{<i>x</i>}Zn_{1â€“<i>x</i>}S Back Contact to CdTe Solar Cells. ACS Applied Energy Materials, 2020, 3, 5427-5438.	5.1	11
18	Heteroepitaxial Integration of ZnGeN₂ on GaN Buffers Using Molecular Beam Epitaxy. Crystal Growth and Design, 2020, 20, 1868-1875.	3.0	24

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19	Six-junction IIIâ€“V solar cells with 47.1% conversion efficiency under 143â€‰Suns concentration. Nature Energy, 2020, 5, 326-335.	39.5	408
20	Nucleation of high-quality GaP on Si through v-groove Si substrates. , 2020, , .		1
21	Templated Vapor-Liquid-Solid Epitaxy of III-V Semiconductors on Silicon. , 2020, , .		0
22	Characterization and modeling of reverseâ€bias breakdown in Cu(In,Ga)Se₂ photovoltaic devices. Progress in Photovoltaics: Research and Applications, 2019, 27, 812-823.	8.1	8
23	Amorphous sulfide heterostructure precursors prepared by radio frequency sputtering. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2019, 37, 051201.	1.2	2
24	Carrier-Transport Study of Gallium Arsenide Hillock Defects. Microscopy and Microanalysis, 2019, 25, 1160-1166.	0.4	4
25	Understanding the charge transport mechanisms through ultrathin SiO<i>x</i> layers in passivated contacts for high-efficiency silicon solar cells. Applied Physics Letters, 2019, 114, .	3.3	41
26	Intrinsic Properties of Individual Inorganic Siliconâ€“Electrolyte Interphase Constituents. ACS Applied Materials & Interfaces, 2019, 11, 46993-47002.	8.0	21
27	Three-dimensional electronic resistivity mapping of solid electrolyte interphase on Si anode materials. Nano Energy, 2019, 55, 477-485.	16.0	56
28	Largeâ€Area Material and Junction Damage in câ€“Si Solar Cells by Potentialâ€Induced Degradation. Solar Rrl, 2019, 3, 1800303.	5.8	7
29	Investigating PID shunting in polycrystalline silicon modules via multiscale, multitechnique characterization. Progress in Photovoltaics: Research and Applications, 2018, 26, 377-384.	8.1	26
30	High-efficiency inverted metamorphic 1.7/1.1 eV GaInAsP/GaInAs dual-junction solar cells. Applied Physics Letters, 2018, 112, .	3.3	47
31	Growth of amorphous and epitaxial ZnSiP₂â€“Si alloys on Si. Journal of Materials Chemistry C, 2018, 6, 2696-2703.	5.5	18
32	An artificial interphase enables reversible magnesium chemistry in carbonate electrolytes. Nature Chemistry, 2018, 10, 532-539.	13.6	347
33	Enabling low-cost III-V/Si integration through nucleation of GaP on v-grooved Si substrates. , 2018, , .		6
34	Surfactant-induced chemical ordering of GaAsN:Bi. Applied Physics Letters, 2018, 113, .	3.3	8
35	Cover Image, Volume 26, Issue 6. Progress in Photovoltaics: Research and Applications, 2018, 26, i-i.	8.1	0
36	Structural and chemical studies of novel 1-eV band gap solar cell materials lattice-matched to GaAs. , 2018, , 229-232.		0

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37	Enhanced Current Collection in 1.7 eV GaInAsP Solar Cells Grown on GaAs by Metalorganic Vapor Phase Epitaxy. IEEE Journal of Photovoltaics, 2017, 7, 927-933.	2.5	26
38	InAlAs photovoltaic cell design for high device efficiency. Progress in Photovoltaics: Research and Applications, 2017, 25, 706-713.	8.1	7
39	Nanoscale insight into the pâ€n junction of alkaliâ€incorporated Cu(In,Ga)Se 2 solar cells. Progress in Photovoltaics: Research and Applications, 2017, 25, 764-772.	8.1	31
40	Low-temperature surface preparation and epitaxial growth of ZnS and Cu2ZnSnS4 on ZnS(1 1 0) and GaP(1 0 0). Journal of Crystal Growth, 2017, 478, 89-95.	1.5	0
41	Large Area Atomically Flat Surfaces via Exfoliation of Bulk Bi₂Se₃ Single Crystals. Chemistry of Materials, 2017, 29, 8472-8477.	6.7	8
42	Reduced dislocation density in GaxIn1âˆ’xP compositionally graded buffer layers through engineered glide plane switch. Journal of Crystal Growth, 2017, 464, 20-27.	1.5	10
43	Growth of lattice-matched GaInAsP grown on vicinal GaAs(001) substrates within the miscibility gap for solar cells. Journal of Crystal Growth, 2017, 458, 1-7.	1.5	21
44	Cover Image, Volume 25, Issue 9. Progress in Photovoltaics: Research and Applications, 2017, 25, i.	8.1	0
45	Analytical (S)TEM Studies of Defects Associated with PID in Stressed Si PV Modules. , 2017, , .		1
46	ZnSiP2 Thin Film Growth for Si-Based Tandem Photovoltaics. , 2017, , .		0
47	Single crystalline substrates for III- V growth via exfoliation of bulk single crystals. , 2017, , .		1
48	Wafer-Bonded AlGaAs///Si Dual-Junction Solar Cells. , 2017, , .		3
49	Measurement of TiO2/p-Si Selective Contact Performance Using a Heterojunction Bipolar Transistor with a Selective Contact Emitter. , 2017, , .		0
50	Investigating PID Shunting in Polycrystalline Silicon Modules via Multi-Scale, Multi-Technique Characterization. , 2017, , .		3
51	Selective area growth of GaAs on Si patterned using nanoimprint lithography. , 2016, , .		6
52	Development of lattice-matched 1.7 eV GaInAsP solar cells grown on GaAs by MOVPE. , 2016, , .		10
53	Synthesis and Characterization of (Sn,Zn)O Alloys. Chemistry of Materials, 2016, 28, 7765-7772.	6.7	16
54	Surfaces and interfaces governing the OMVPE growth of APD-free GaP on AsH3-cleaned vicinal Si(100). Journal of Crystal Growth, 2016, 452, 235-239.	1.5	10

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55	Solar energy conversion properties and defect physics of ZnSiP₂. Energy and Environmental Science, 2016, 9, 1031-1041.	30.8	49
56	Implementation of tunneling pasivated contacts into industrially relevant n-Cz Si solar cells. , 2015, , .		11
57	Single crystal growth and phase stability of photovoltaic grade ZnSiP2 by flux technique. , 2015, , .		5
58	Effects of Disorder on Carrier Transport in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mrow><mml:msub><mml:mrow><mml:mi>Cu</mml:mi></mml:mrow><mml:mrow><mml:mn>2</r Physical Review Applied, 2015, 4, .	3.8	73
59	Growth of antiphase-domain-free GaP on Si substrates by metalorganic chemical vapor deposition using an <i>in situ</i> AsH3 surface preparation. Applied Physics Letters, 2015, 107, .	3.3	51
60	Spontaneous lateral phase separation of AlInP during thin film growth and its effect on luminescence. Journal of Applied Physics, 2015, 118, .	2.5	15
61	III-V/Si wafer bonding using transparent, conductive oxide interlayers. Applied Physics Letters, 2015, 106, .	3.3	20
62	Studying Perovskite-based Solar Cells with Correlative In-Situ Microscopy. Microscopy and Microanalysis, 2015, 21, 969-970.	0.4	11
63	Theoretical and experimental study of highly textured GaAs on silicon using a graphene buffer layer. Journal of Crystal Growth, 2015, 425, 268-273.	1.5	25
64	Investigation of GaP/Si heteroepitaxy on MOCVD prepared Si(100) surfaces. , 2015, , .		2
65	Indium zinc oxide mediated wafer bonding for IIIâ€“V/Si tandem solar cells. , 2015, , .		8
66	Development of ZnSiP$_{mathbf 2}$ for Si-Based Tandem Solar Cells. IEEE Journal of Photovoltaics, 2015, 5, 17-21.	2.5	19
67	Combinatorial insights into doping control and transport properties of zinc tin nitride. Journal of Materials Chemistry C, 2015, 3, 11017-11028.	5.5	128
68	Comparison of thin epitaxial film silicon photovoltaics fabricated on monocrystalline and polycrystalline seed layers on glass. Progress in Photovoltaics: Research and Applications, 2015, 23, 909-917.	8.1	9
69	Improved quantum dot stacking for intermediate band solar cells using strain compensation. Nanotechnology, 2014, 25, 445402.	2.6	17
70	Low temperature Si/SiO<inf>x</inf>/pc-Si passivated contacts to n-type Si solar cells. , 2014, , .		11
71	Carrier-selective, passivated contacts for high efficiency silicon solar cells based on transparent conducting oxides. , 2014, , .		31
72	Carrier Selective, Passivated Contacts for High Efficiency Silicon Solar Cells based on Transparent Conducting Oxides. Energy Procedia, 2014, 55, 733-740.	1.8	24

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73	Doping dependence and anisotropy of minority electron mobility in molecular beam epitaxy-grown p type GaInP. Applied Physics Letters, 2014, 105, .	3.3	13
74	Minority carrier lifetimes in 1.0-eV p-In<inf>0.27</inf>Ga<inf>0.73</inf>As layers grown on GaAs substrates. , 2014, , .		0
75	Bulk defect generation during B-diffusion and oxidation of CZ wafers: Mechanism for degrading solar cell performance. , 2014, , .		3
76	Lattice-Mismatched 0.7-eV GaInAs Solar Cells Grown on GaAs Using GaInP Compositionally Graded Buffers. IEEE Journal of Photovoltaics, 2014, 4, 190-195.	2.5	39
77	GaSb/InGaAs quantum dotâ€“well hybrid structure active regions in solar cells. Solar Energy Materials and Solar Cells, 2013, 114, 165-171.	6.2	31
78	GaSb/InGaAs quantum dot-well solar cells. , 2013, , .		1
79	Epitaxial growth of InGaAs on MgAl2O4 spinel for one-sun photovoltaics. Journal of Crystal Growth, 2013, 363, 40-43.	1.5	1
80	Ordering-enhanced dislocation glide in III-V alloys. Journal of Applied Physics, 2013, 114, .	2.5	20
81	Electron microscopy study of individual grain boundaries in Cu<inf>2</inf>ZnSnSe<inf>4</inf> thin films. , 2013, , .		0
82	The influence of atomic ordering on strain relaxation during the growth of metamorphic solar cells. Journal of Physics: Conference Series, 2013, 471, 012006.	0.4	4
83	Defect characterization in compositionally graded InGaAs layers on GaAs(001) grown by MBE. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1640-1643.	0.8	4
84	Spectral optical properties of Cu_2ZnSnS_4 thin film between 073 and 65 eV. Optics Express, 2012, 20, A327.	3.4	32
85	Control of misfit dislocation glide plane distribution during strain relaxation of CuPt-ordered GaInAs and GaInP. Journal of Applied Physics, 2012, 112, 023520.	2.5	32
86	Coincident site lattice-matched InGaN on (111) spinel substrates. Applied Physics Letters, 2012, 100, 152106.	3.3	5
87	Dielectric function spectra and critical-point energies of Cu2ZnSnSe4 from 0.5 to 9.0 eV. Journal of Applied Physics, 2012, 111, .	2.5	53
88	Atomic ordering and phase separation in MBE GaAs1â^’xBix. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, 03C121.	1.2	53
89	Optical anisotropy and charge-transfer transition energies in BiFeO<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow /><mml:mrow><mml:mn>3</mml:mn></mml:mrow></mml:msub></mml:mrow></mml:math>from 1.0 to 5.5 eV. Physical Review B, 2011, 83, .	3.2	38
90	Effects of substrate orientation on aluminum grown on MgAl2O4 spinel using molecular beam epitaxy. Journal of Crystal Growth, 2011, 314, 298-301.	1.5	0

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91	Single-crystalline aluminum grown on MgAl2O4 spinel using molecular-beam epitaxy. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, 03C128.	1.2	2
92	Above-band-gap dielectric functions of ZnGeAs<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow /><mml:mrow><mml:mn>2</mml:mn></mml:mrow></mml:msub></mml:mrow></mml:math>: Ellipsometric measurements and quasiparticle self-consistent<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mi mathvarian	3.2	10
93	Atomic scale characterization of compound semiconductors using atom probe tomography. , 2011, , .		3
94	Transient Absorption for Characterization of Quantum Dot Intermediate Band Solar Cells. Materials Research Society Symposia Proceedings, 2011, 1289, 402.	0.1	0
95	Use of a GaAsSb buffer layer for the formation of small, uniform, and dense InAs quantum dots. Applied Physics Letters, 2010, 96, .	3.3	40
96	Nanocomposite Counter Electrode Materials for Electrochromic Windows. Journal of the Electrochemical Society, 2010, 157, H328.	2.9	49
97	Oxidation and characterization of AlInP under light-soaked, damp heat conditions. , 2010, , .		3
98	Complex dielectric function and refractive index spectra of epitaxial CdO thin film grown on r-plane sapphire from 0.74 to 6.45 eV. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2010, 28, 1120-1124.	1.2	21
99	Transient absorption for characterization of intermediate band solar cells. , 2010, , .		0
100	Electrodeposited Biaxially Textured Buffer Layers for YBCO Superconductors. IEEE Transactions on Applied Superconductivity, 2009, 19, 3451-3454.	1.7	12
101	CuPt ordering in high bandgap GaxIn1â^’xP alloys on relaxed GaAsP step grades. Journal of Applied Physics, 2009, 106, .	2.5	22
102	Transmission electron microscope study on electrodeposited Gd2O3 and Gd2Zr2O7 buffer layers for YBa2Cu3O7â^’Î´ superconductors. Physica C: Superconductivity and Its Applications, 2008, 468, 1092-1096.	1.2	11
103	In situ stress measurement for MOVPE growth of high efficiency lattice-mismatched solar cells. Journal of Crystal Growth, 2008, 310, 2339-2344.	1.5	43
104	Intragrain defects in polycrystalline silicon thin-film solar cells on glass by aluminum-induced crystallization and subsequent epitaxy. Thin Solid Films, 2008, 516, 6409-6412.	1.8	18
105	Theoretical and experimental examination of the intermediate-band concept for strain-balanced (In,Ga)As/Ga(As,P) quantum dot solar cells. Physical Review B, 2008, 78, .	3.2	215
106	40.8% efficient inverted triple-junction solar cell with two independently metamorphic junctions. Applied Physics Letters, 2008, 93, .	3.3	433
107	Inverted GaInP / (In)GaAs / InGaAs triple-junction solar cells with low-stress metamorphic bottom junctions. Conference Record of the IEEE Photovoltaic Specialists Conference, 2008, , .	0.0	12
108	Efficient Photoinduced Charge Injection from Chemical Bath Deposited CdS into Mesoporous TiO₂ Probed with Time-Resolved Microwave Conductivity. Journal of Physical Chemistry C, 2008, 112, 7742-7749.	3.1	35

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109	Modulated Structures and Atomic Ordering in InPySb1-yLayers Grown by Organometallic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2008, 47, 2209-2212.	1.5	4
110	Modulated Contrast and Associated Diffracted Intensity of GaPySb1-y Layers Grown Using Organometallic Vapor Phase Epitaxy. Journal of the Korean Physical Society, 2008, 52, 471-475.	0.7	2
111	Atom Probe Analysis of IIIâ€"V and Si-Based Semiconductor Photovoltaic Structures. Microscopy and Microanalysis, 2007, 13, 493-502.	0.4	47
112	Optical anisotropy of InGaAsâˆ•Ga(As,P) quantum dots grown on GaAs (311)B substrates. Applied Physics Letters, 2007, 91, 223109.	3.3	3
113	Optimization of crystalline tungsten oxide nanoparticles for improved electrochromic applications. Solid State Ionics, 2007, 178, 895-900.	2.7	48
114	Nanocrystalline TiO2Solar Cells Sensitized with InAs Quantum Dotsâ€. Journal of Physical Chemistry B, 2006, 110, 25451-25454.	2.6	443
115	PbTe Colloidal Nanocrystals:Â Synthesis, Characterization, and Multiple Exciton Generation. Journal of the American Chemical Society, 2006, 128, 3241-3247.	13.7	660
116	Lattice-mismatched GaAsP Solar Cells Grown on Silicon by OMVPE. , 2006, , .		60
117	0.7-eV GaInAs Junction for a GaInP/GaAs/GaInAs(1eV)/GaInAs(0.7eV) Four-Junction Solar Cell. , 2006, , .		19
118	Atomic ordering-induced band gap reductions in GaAsSb epilayers grown by molecular beam epitaxy. Journal of Applied Physics, 2005, 97, 063701.	2.5	16
119	Spontaneous lateral modulation in short-period superlattices investigated by grazing-incidence x-ray diffraction. Physical Review B, 2005, 72, .	3.2	2
120	X-ray diffraction on laterally modulated (InAs)nâˆ•(AlAs)m short-period superlattices. Journal of Applied Physics, 2004, 96, 4833-4838.	2.5	5
121	Quadruple-period ordering in MBE GaAsSb alloys. Materials Research Society Symposia Proceedings, 2003, 794, 49.	0.1	0
122	Effects of Substrate Orientation on the Spontaneous Ordering of GaAsSb Epilayers Grown by Molecular Beam Epitaxy. Materials Research Society Symposia Proceedings, 2003, 794, 1.	0.1	0
123	Growth Model for Atomic Ordering: The Case for Quadruple-Period Ordering in GaAsSb Alloys. Physical Review Letters, 2003, 90, 026102.	7.8	8
124	Direct measurement of polarization resolved transition dipole moment in InGaAs/GaAs quantum dots. Applied Physics Letters, 2003, 82, 4552-4554.	3.3	45
125	Observation of large optical anisotropy and valence band splitting in AlInAs self-assembled lateral quantum wells. Applied Physics Letters, 2002, 80, 243-245.	3.3	21
126	Lateral composition modulation in(InAs)n/(AlAs)mshort-period superlattices investigated by high-resolution x-ray scattering. Physical Review B, 2002, 66, .	3.2	20

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127	Two-dimensional array of self-assembled AlInAs quantum wires. Applied Physics Letters, 2002, 81, 529-531.	3.3	5
128	Initiation and evolution of phase separation in heteroepitaxial InAlAs films. Applied Physics Letters, 2002, 80, 3292-3294.	3.3	29
129	Temperature dependence of the band gap of GaAsSb epilayers. Journal of Applied Physics, 2002, 92, 6939-6941.	2.5	28
130	Bimodal size distribution of self-assembledInxGa1âˆ'xAsquantum dots. Physical Review B, 2002, 66, .	3.2	34
131	Formation of InAs/GaAs quantum dots by dewetting during cooling. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2002, 20, 1489.	1.6	6
132	X-Ray Characterization of Nanostructured Semiconductor Short-Period Superlattices. Materials Research Society Symposia Proceedings, 2002, 749, 1.	0.1	0
133	Optical properties of self-assembled lateral superlattices in AlInAs epitaxial layers and AlAs/InAs short-period superlattices. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 88, 118-124.	3.5	4
134	The Nature and Origin of Atomic Ordering in Group III-V Antimonide Semiconductor Alloys. , 2002, , 45-97.		2
135	Epitaxial growth of BGaAs and BGaInAs by MOCVD. Journal of Crystal Growth, 2001, 225, 372-376.	1.5	60
136	Growth of bulk and superlattice GaAsSb layers on InP. Journal of Materials Science Letters, 2001, 20, 677-680.	0.5	1
137	Growth of bulk and superlattice GaAsSb layers on InP. Journal of Materials Science Letters, 2001, 20, 363-366.	0.5	3
138	Quadruple-period ordering along [110] in aGaAs0.87Sb0.13alloy. Physical Review B, 2001, 63, .	3.2	11
139	X-ray analysis of spontaneous lateral modulation in (InAs)n/(AlAs)m short-period superlattices. Applied Physics Letters, 2001, 78, 219-221.	3.3	7
140	Comparison of hydrazine, dimethylhydrazine, and t-butylamine nitrogen sources for MOVPE growth of GaInNAs for solar cells. Journal of Crystal Growth, 2000, 208, 11-17.	1.5	21
141	Effect of surface steps on the microstructure of lateral composition modulation. Applied Physics Letters, 2000, 77, 669-671.	3.3	15
142	Optical properties of spontaneous lateral composition modulation in AlAs/InAs short-period superlattices. Applied Physics Letters, 2000, 77, 1765.	3.3	10
143	Relationship between the lateral length and thickness of the platelets in naturally occurring strained layer superlattice structures. Journal of Applied Physics, 2000, 88, 5733-5736.	2.5	3
144	BGaInAs alloys lattice matched to GaAs. Applied Physics Letters, 2000, 76, 1443-1445.	3.3	94

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145	Electronic structure of self-organized InAs/GaAs quantum dots bounded by{136}facets. Physical Review B, 2000, 61, 2784-2793.	3.2	53
146	Electronic structure and optical polarization anisotropy of self-organized InAs/GaAs quantum dots. , 1999, , .		0
147	Resonance Raman scattering studies of composition-modulated GaP/InP short-period superlattices. Physical Review B, 1999, 60, 4883-4888.	3.2	9
148	Ge-related faceting and segregation during the growth of metastable (GaAs)1â^'x(Ge2)x alloy layers by metalâ€"organic vapor-phase epitaxy. Applied Physics Letters, 1999, 74, 1382-1384.	3.3	34
149	Photoluminescence studies of lateral composition modulated short-period AlAs/InAs superlattices. Thin Solid Films, 1999, 357, 31-34.	1.8	4
150	Title is missing!. Journal of Materials Science: Materials in Electronics, 1999, 10, 191-197.	2.2	9
151	The shape of self-assembled InAs islands grown by molecular beam epitaxy. Journal of Electronic Materials, 1999, 28, 481-485.	2.2	14
152	Characterizing composition modulations in InAs/AlAs short-period superlattices. Physical Review B, 1999, 60, 13619-13635.	3.2	45
153	The Nature and Origin of Lateral Composition Modulations in Short-Period Strained-Layer Superlattices. Materials Research Society Symposia Proceedings, 1999, 583, 297.	0.1	11
154	Reciprocal-Space and Real-Space Analyses of Compositional Modulation in InAs/AlAs Short-Period Superlattices. Materials Research Society Symposia Proceedings, 1999, 583, 333.	0.1	2
155	Profiling Composition Variations in Composition-Modulated GaP/InP Short-Period Superlattices Using Resonance Raman Scattering. Materials Research Society Symposia Proceedings, 1999, 583, 361.	0.1	0
156	Strain-dependent morphology of spontaneous lateral composition modulations in (AlAs)m(InAs)n short-period superlattices grown by molecular beam epitaxy. Applied Physics Letters, 1998, 73, 1844-1846.	3.3	45
157	Laterally modulated composition profiles in AlAs/InAs short-period superlattices. Journal of Applied Physics, 1998, 84, 6088-6094.	2.5	34
158	The evaluation and control of quantum wells and superlattices of IIIâ€"V narrow gap semiconductors. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1997, 44, 260-265.	3.5	4
159	Study of misfit dislocations by EBIC, CL and HRTEM in GaAs/InGaAs lattice-strained multi-quantum well p-i-n solar cells. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1996, 42, 43-51.	3.5	15
160	Direct manifestation of the Fermi pressure in a two-dimensional electron system. Physical Review B, 1996, 54, 7651-7653.	3.2	7
161	Intersubband Raman spectroscopy of two-dimensional electron gases in GaSb/InAs quantum wells. Semiconductor Science and Technology, 1996, 11, 1137-1145.	2.0	7
162	Photo- and electro-luminescence studies of uncooled arsenic-rich In(As,Sb) strained layer superlattice light-emitting diodes for the 4-12-Î¼m band. , 1995, , .		2

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163	Magnetotransport measurements on InAs-GaSb quantum wells with the application of hydrostatic pressure. Journal of Physics and Chemistry of Solids, 1995, 56, 445-451.	4.0	8
164	Midinfrared picosecond spectroscopy studies of Auger recombination in InSb. Physical Review B, 1995, 52, 2516-2521.	3.2	38
165	4-11 mu m infrared emission and 300 K light emitting diodes from arsenic-rich InAs1-xSbxstrained layer superlattices. Semiconductor Science and Technology, 1995, 10, 1177-1180.	2.0	48
166	Atomic ordering in molecular beam epitaxial InAsySb1â^'ynatural strained layer superlattices and homogeneous layers. Applied Physics Letters, 1994, 64, 3593-3595.	3.3	47
167	Atomic ordering and domain structures in metal organic chemical vapor deposition grown InGaAs (001) layers. Journal of Applied Physics, 1994, 75, 7852-7865.	2.5	48
168	Mechanism for CuPt-type ordering in mixed IIIâ€"V epitaxial layers. Journal of Crystal Growth, 1994, 140, 249-263.	1.5	107
169	Quantum transport in strained layer superlattices. Surface Science, 1994, 305, 337-342.	1.9	3
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